# SK100B



# SEMITOP<sup>®</sup> 2

### **Bridge Rectifier**

#### SK100B

Target Data

#### Features

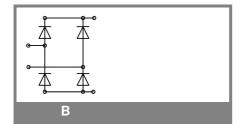
- Compact design
- One screw mounting
- Heat transfer and insulation through direct copper bonded aluminium oxide ceramic (DCB)
- Up 1600V reverse voltage
  Ligh surge surgent
- High surge current
- Glass passived diode chips
- UL recognized, file no. E 63 532

#### **Typical Applications**

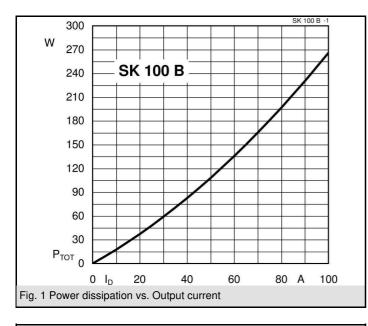
- Input rectifier for power supplies
- Rectifier
- 1)  $V_F$ ,  $V_{(TO)}$ ,  $r_T$  = chip level value

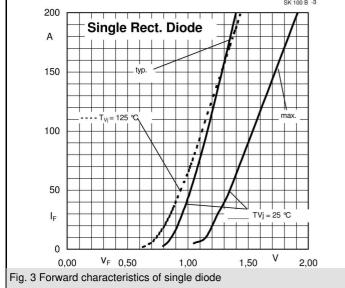
V <sub>RSM</sub> V	V <sub>RRM</sub> , V <sub>DRM</sub> V	I <sub>D</sub> = <sup>51</sup> A (full conduction) (T <sub>s</sub> = 80 °C)
900	800	SK100B08
1300	1200	SK100B12
1700	1600	SK100B16

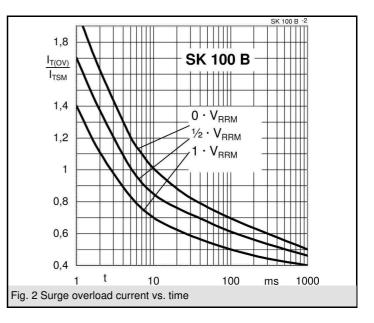
Symbol	Conditions	Values	Units
I <sub>D</sub>	T <sub>s</sub> = 80 °C	100	А
I <sub>FSM</sub>	T <sub>vi</sub> = 25 °C; 10 ms	1000	А
-	T <sub>vi</sub> = 150 °C; 10 ms	890	A
i²t	T <sub>vj</sub> = 25 °C; 8,310 ms	5000	A²s
	T <sub>vj</sub> = 125 °C; 8,310 ms	3960	A²s
V <sub>F</sub>	T <sub>vi</sub> = 25 °C; I <sub>F</sub> = 40 A	max. 1,21	V
V <sub>(TO)</sub>	T <sub>vi</sub> = 125 °C	max. 0,83	V
r <sub>T</sub>	T <sub>vi</sub> = 125 °C	max. 3,9	mΩ
I <sub>RD</sub>	$T_{vj} = 150 \text{ °C}; V_{DD} = V_{DRM}; V_{RD} = V_{RRM}$	max. 1,1	mA
			mA
R <sub>th(j-s)</sub>	per diode	1	K/W
	per module	0,25	K/W
T <sub>solder</sub>	terminals, 10s	260	°C
T <sub>vj</sub>		-40+150	°C
T <sub>stg</sub>		-40+125	°C
V <sub>isol</sub>	a. c. 50 Hz; r.m.s.; 1 s / 1 min.	3000 ( 2500 )	V
Ms	mounting torque to heatsink	2	Nm
M <sub>t</sub>			
m	approx. weight	19	g
Case	SEMITOP <sup>®</sup> 2	Т 6	

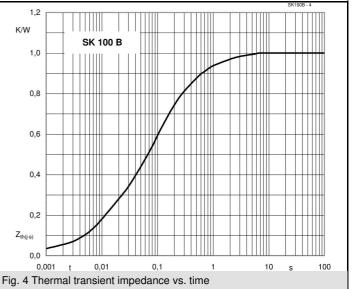


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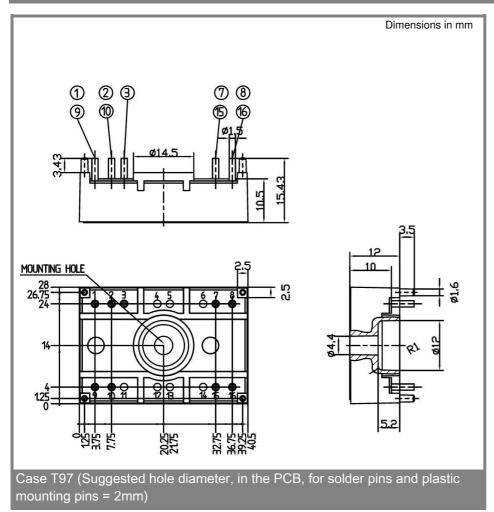








### **SK100B**



9,10 • 1,2,3 9,10 • 15,16 • 7,8 Case T97 B

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